

ABSTRACT OF THE DISCLOSURE

In the semiconductor device, in order to meet the demand of reduced diameter of a contact hole along with the miniaturization of the semiconductor device, an anti-HF side wall film which is not etched by a hydrofluoric acid, formed of an isolating film such as nitride film, is provided on the side wall of contact hole. Further, a second impurity region which is connected to one of the pair of n type source/drain regions and a first impurity region reaching a p type isolation region are provided in silicon substrate 1 near the lower end of contact hole. Because of this structure, it becomes possible to prevent expansion of the diameter for forming the interconnection layer, as desired in the miniaturized semiconductor device, and therefore a semiconductor device and manufacturing method thereof which stabilize operation characteristic of the semiconductor device can be provided.

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